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The technical content of this TAOS datasheet is still valid.

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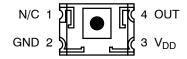
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- Converts Light Intensity to Output Voltage
- Monolithic Silicon IC Containing Photodiode, Operational Amplifier, and Feedback Components
- High Sensitivity
- Single Voltage Supply Operation (2.7 V to 5.5 V)
- High Irradiance Responsivity . . . Typical 680 mV/(μW/cm²) at λ_p = 640 nm
- Low Noise (200 μVrms Typ to 1 kHz)
- Rail-to-Rail Output
- High Power-Supply Rejection (35 dB at 1 kHz)
- Low-Profile Surface-Mount Package
- RoHS Compliant

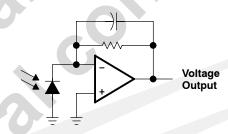
PACKAGE T 4-LEAD SMD (TOP VIEW)



Description

The TSL257T is a high-sensitivity low-noise light-to-voltage optical converter that combines a photodiode and a transimpedance amplifier on a single monolithic CMOS integrated circuit. Output voltage is directly proportional to light intensity (irradiance) on the photodiode. The TSL257T has a transimpedance gain of 320 $M\Omega$. The device has improved offset voltage stability and low power consumption and is supplied in a compact 4-lead surface-mount package.

Functional Block Diagram



Terminal Functions

TERMINAL				
NAME	T PKG NO.	DESCRIPTION		
GND	2	Power supply ground (substrate). All voltages are referenced to GND.		
OUT	4	Output voltage.		
V_{DD}	3	Supply voltage.		
N/C	1	No connection.		

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Absolute Maximum Ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V _{DD} (see Note 1)	6 V
Output current, I _O	±10 mA
Duration of short-circuit current at (or below) 25°C	5 s
Operating free-air temperature range, T _A	25°C to 85°C
Storage temperature range, T _{stq}	25°C to 85°C
Solder conditions in accordance with JEDEC-J-SRD-020A, maximum temperature	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltages are with respect to GND.

Recommended Operating Conditions

	MIN	MAX	UNIT
Supply voltage, V _{DD}	2.7	5.5	V
Operating free-air temperature, T _A	0	70	°C

Electrical Characteristics at V_{DD} = 5 V, T_A = 25°C, λ_p = 640 nm, R_L = 10 k Ω (unless otherwise noted) (see Notes 2, 3, and 4)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_D	Dark voltage	E _e = 0	0		15	mV
V	Marian and a day to although a social	V _{DD} = 4.5 V, No Load		4.49		V
V _{OM}	Maximum output voltage swing	$V_{DD} = 4.5 \text{ V}, \qquad R_L = 10 \text{ k}\Omega$	4	4.2		V
Vo	Output voltage	$E_e = 2.93 \mu W/cm^2$	1.5	2	2.5	V
α_{VD}	Temperature coefficient of dark voltage (VD)	T _A = 0°C to 70°C		-15		μV/°C
R _e	Irradiance responsivity	See Note 5		680		$\text{mV/(}\mu\text{W/cm}^2\text{)}$
PSRR	Power supply rejection ratio	f _{ac} = 100 Hz, see Note 6		55		dB
		f _{ac} = 1 kHz, see Note 6		35		dB
I_{DD}	Supply current	$E_e = 2.93 \ \mu W/cm^2$		2	3.8	mA

NOTES: 2. Measured with $R_L = 10 \text{ k}\Omega$ between output and ground.

- 3. Optical measurements are made using small-angle incident radiation from a light-emitting diode (LED) optical source.
- 4. The input irradiance E_e is supplied by an AlInGaP LED with peak wavelength λ_p = 640 nm.
- Irradiance responsivity is characterized over the range V_O = 0.1 V to 4.5 V. The best-fit straight line of Output Voltage V_O versus
 Irradiance E_e over this range will typically have a positive extrapolated V_O value for E_e = 0.
- 6. Power supply rejection ratio PSRR is defined as 20 log $(\Delta V_{DD}(f)/\Delta V_{O}(f))$ with $V_{DD}(f=0)=5$ V and $V_{O}(f=0)=2$ V.

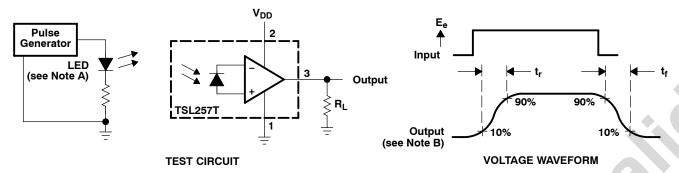
Switching Characteristics at V_{DD} = 5 V, T_A = 25°C, λ_p = 640 nm, R_L = 10 k Ω (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _r	Output pulse rise time, 10% to 90% of final value	See Note 10 and Figure 1		160	250	μs
t _f	Output pulse fall time, 10% to 90% of final value	See Note 10 and Figure 1		150	250	μs
ts	Output settling time to 1% of final value	See Note 10 and Figure 1		330		μs
	Integrated noise voltage	$f = dc to 1 kHz$ $E_e = 0$		200		μVrms
	7 (0)	f = 10 Hz		6		
Vn	Output noise voltage, rms	f = 100 Hz		6		μV/√ Hz rms
		$f = 1 \text{ kHz}$ $E_e = 0$		7		

NOTE 7: Switching characteristics apply over the range $V_0 = 0.1 \text{ V}$ to 4.5 V.



PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The input irradiance is supplied by a pulsed AlInGaP light-emitting diode with the following characteristics: $\lambda_p = 640$ nm, $t_r < 1 \mu s$, $t_f < 1 \mu s$.
 - B. The output waveform is monitored on an oscilloscope with the following characteristics: $t_r < 100$ ns, $Z_i \ge 1$ M Ω , $C_i \le 20$ pF.

Figure 1. Switching Times

TYPICAL CHARACTERISTICS

PHOTODIODE SPECTRAL RESPONSIVITY 1 T_A = 25°C 0.8 Relative Responsivity 0.6 0.4 0.2 300 400 500 600 700 800 900 1000 1100 λ - Wavelength - nm Figure 2

FREQUENCY 80 70 Power Supply Rejection Ratio — dB 60 50 40 30 20 10 10⁵ 102 10³ 10⁴ 10 106 f - Frequency - Hz

Figure 3

POWER SUPPLY REJECTION RATIO

TYPICAL CHARACTERISTICS

DARK VOLTAGE vs FREE-AIR TEMPERATURE

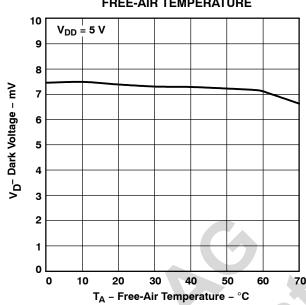
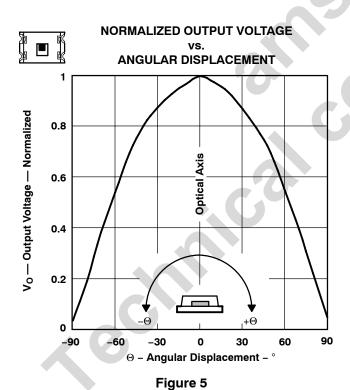


Figure 4



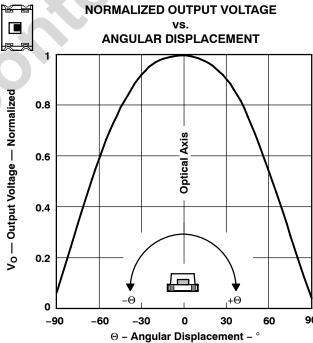
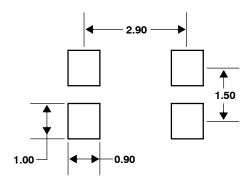


Figure 6

APPLICATION INFORMATION

PCB Pad Layout

Suggested PCB pad layout guidelines for the T package are shown in Figure 7.



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

Figure 7. Suggested T Package PCB Layout

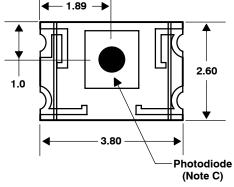
MECHANICAL DATA

The TSL257T is supplied in a low-profile surface-mount package. This package contains no lead (Pb).

PACKAGE T

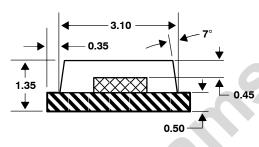
Four-Lead Surface Mount Device

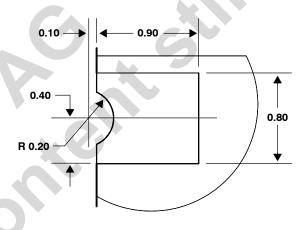
TOP VIEW 1.89 -



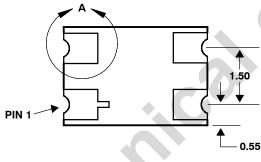
DETAIL A: TYPICAL PACKAGE TERMINAL

SIDE VIEW





BOTTOM VIEW

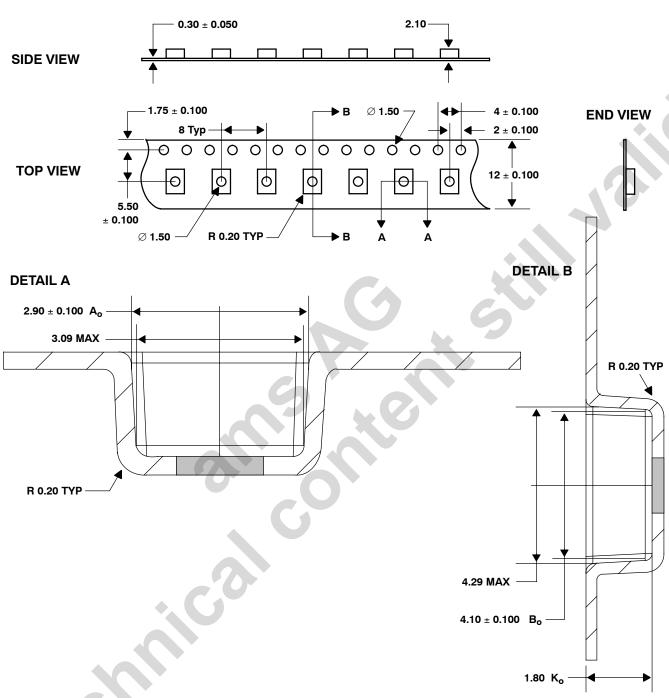




- NOTES: A. All linear dimensions are in millimeters.
 - B. Terminal finish is gold.
 - C. The center of the 0.75 mm diameter integrated photodiode active area is typically located 0.1 mm above the center of the package.
 - D. Dimension tolerance is \pm 0.15 mm.
 - E. This drawing is subject to change without notice.

Figure 8. Package T — Four-Lead Surface Mount Device Packaging Configuration

MECHANICAL DATA



NOTES: A. All linear dimensions are in millimeters.

- B. The dimensions on this drawing are for illustrative purposes only. Dimensions of an actual carrier may vary slightly.
- C. Symbols on drawing A_o, B_o, and K_o are defined in ANSI EIA Standard 481-B 2001.
- D. Each reel is 178 millimeters in diameter and contains 1000 parts.
- E. TAOS packaging tape and reel conform to the requirements of EIA Standard 481-B.
- F. In accordance with EIA standard, device pin 1 is located next to the sprocket holes in the tape.
- G. This drawing is subject to change without notice.

Figure 9. Four Lead Surface Mount Package Carrier Tape



MANUFACTURING INFORMATION

The reflow profile specified here describes expected maximum heat exposure of devices during the solder reflow process of the device on a PWB. Temperature is measured at the top of the device. Devices should be limited to one pass through the solder reflow profile.

Table 1. TSL257T Solder Reflow Profile

PARAMETER	REFERENCE	TSL257T
Average temperature gradient in preheating		2.5°C/sec
Soak time	t _{soak}	2 to 3 minutes
Time above T ₁ , 217°C	t ₁	Max 60 sec
Time above T ₂ , 230°C	t ₂	Max 50 sec
Time above T ₃ , (T _{peak} -10°C)	t ₃	Max 10 sec
Peak temperature in reflow	T _{peak}	260° C (-0°C/+5°C)
Temperature gradient in cooling		Max -5°C/sec

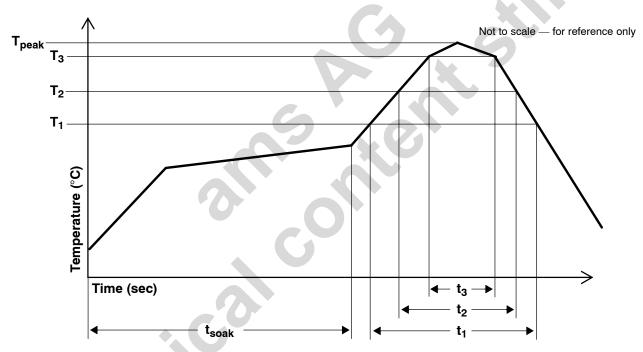


Figure 10. TSL257T Solder Reflow Profile

MANUFACTURING INFORMATION

Moisture Sensitivity

Optical characteristics of the device can be adversely affected during the soldering process by the release and vaporization of moisture that has been previously absorbed into the package molding compound. To ensure the package molding compound contains the smallest amount of absorbed moisture possible, each device is dry–baked prior to being packed for shipping. Devices are packed in a sealed aluminized envelope with silica gel to protect them from ambient moisture during shipping, handling, and storage before use.

This package has been assigned a moisture sensitivity level of MSL 3 and the devices should be stored under the following conditions:

Temperature Range 5°C to 50°C Relative Humidity 60% maximum

Total Time 6 months from the date code on the aluminized envelope — if unopened

Opened Time 168 hours or fewer

Rebaking will be required if the devices have been stored unopened for more than 6 months or if the aluminized envelope has been open for more than 168 hours. If rebaking is required, it should be done at 90°C for 4 hours.



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